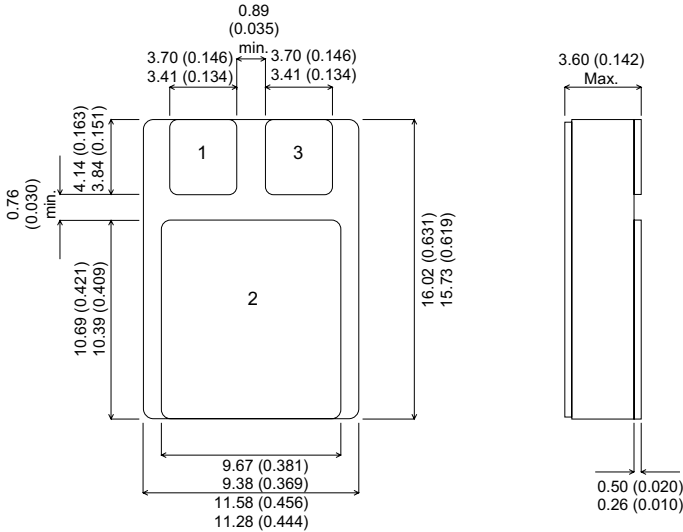


MECHANICAL DATA

Dimensions in mm



SMD1

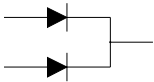
**DUAL SCHOTTKY
 BARRIER DIODE IN A
 SMD1 CERAMIC SURFACE
 MOUNT PACKAGE
 FOR HI-REL APPLICATIONS**

FEATURES

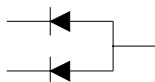
- HERMETIC CERAMIC PACKAGE
- ISOLATED CASE
- SCREENING OPTIONS AVAILABLE
- OUTPUT CURRENT 16A
- LOW V_F
- LOW LEAKAGE

ELECTRICAL CONNECTIONS

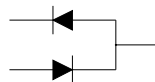
Common Cathode **Common Anode** **Series Connection**
 SB16-100M-SMD SB16-100A-SMD SB16-100R-SMD



1 = A₁ Anode 1
 2 = K Cathode
 3 = A₂ Anode 2



1 = K₁ Cathode 1
 2 = A Anode
 3 = K₂ Cathode 2



1 = K₁ Cathode 1
 2 = Centre Tap
 3 = A₂ Anode

ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^\circ C$ unless otherwise stated)

		SB16-100M-SMD SB16-100A-SMD SB16-100R-SMD
V_{RRM}	Peak Repetitive Reverse Voltage	100V
V_{RSM}	Peak Non-Repetitive Reverse Voltage	100V
V_R	Continuous Reverse Voltage	100V
I_O	Output Current	16A
I_{FSM}	Peak Non-Repetitive Surge Current (50Hz)	245A
T_{STG}	Storage Temperature Range	-55°C to 150°C
T_J	Maximum Operating Junction Temperature	150°C/W

ELECTRICAL CHARACTERISTICS (Per Diode)($T_{CASE} = 25^{\circ}C$ unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_F Forward Voltage	$I_F = 8A$ $T_J = 150^{\circ}C$			0.8	V
	$I_F = 16A$ $T_J = 25^{\circ}C$			1.0	
I_R Reverse Current	$V_R = V_{RRM}$ $T_J = 150^{\circ}C$			30	mA
	$V_R = V_{RRM}$ $T_J = 25^{\circ}C$			500	μA
C_d Junction Capacitance	$V_R = 5 V$ $f = 1 MHz$		500		pF

Pulse test $t_p=300\mu s$ $\delta \leq 2\%$

Parameter	Unit
$R_{TH(j-a)}$ Maximum Thermal Resistance Junction To Case	both diodes 1.4 per diode 2.3 $^{\circ}C/W$
$R_{TH(j-c)}$ Maximum Thermal Resistance Junction To Case	1.3 $^{\circ}C/W$